

Controlling of exciton condensate by external fields and phonon laser

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The novel method of observation and controlling of Bose-Einstein condensation in the system of spatially and momentum-space indirect excitons in coupled quantum wells using in-plane magnetic and normal electric fields is proposed. Fields are used for exciton dispersion engineering. In the presence of in-plane magnetic field ground state of spatially indirect exciton becomes also indirect in the momentum space. Manipulation of electric field magnitude is used for tuning to resonance of transition of "dark" long-life spatially and momentum-space indirect exciton in condensate into spatially and momentum-space direct exciton in radiative zone, with phonon creation, and with subsequent recombination of the direct exciton in radiative zone. Recombination rate of indirect excitons in condensate according to proposed scheme sharply rises at resonance. As a result besides enhanced spectral narrow photoluminescence connected with recombination of direct exciton in radiative zone with specific angular dependence, almost monochromatic and unidirectional beam of phonons appears. An opportunity of obtaining of "phonon laser" radiation on the basis of this effect is considered.

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The system perspective for observation of different phases of excitons is the system of spatially indirect excitons (SIE) in coupled quantum wells (CQW) (see Ref. [1,3] and references therein). The point is that for the system of SIE in CQW - with spatially separated electron and hole (e and h) - recombination is suppressed by exponentially small overlapping of e and h wave functions. Thus, the case can be easily achieved when the relaxation times of electrons, holes or excitons is sufficiently smaller than their lifetime. Therefore, there is an opportunity for reliable observation of different equilibrium exciton phases. In superfluid phase of the system of spatially separated e and h interesting phenomena can be observed, such as nondissipative electric currents in each quantum well, Josephson effects etc. [2,14]. Very interesting recent experiments [5,6] (see also essential previous works [7]) bear witness to an existence of coherent effects in SIE system at low temperatures.

In this paper we propose new method of the observation and controlling of coherent phase of SIE by external fields. We consider direct-gap 1S -excitons in GaAs-AlGaAs CQW. In-plane magnetic field shifts SIE dispersion minimum, where Bose-Einstein condensate (BEC) of SIE forms, out of the radiative zone. Energy of SIE in BEC is linear dependent on magnitude of normal electric field. Thus changing the electric field value enables one to tune the system of indirect excitons in condensate to resonance of process of transformation into spatially and momentum-space direct excitons (SDE) in radiative zone, by emitting phonons, and subsequent recombination of the SDE. It occurs that photoluminescence (PL) of indirect excitons in condensate according to proposed scheme sharply rises and has specific angular dependence at resonance. Besides, almost monochromatic and unidirectional beam of phonons appears. Possibility of phonon laser creation using this effect is discussed.

There are four different bound states for a pair of e and h in CQW in the absence of external fields (Fig.1 a). Two of them, with e and h in the same quantum well, correspond to SDE placed in one of two quantum wells. The other two bound states correspond to SIE with e and h in different quantum wells. As a result of spatial separation of e and h SIE has normal to CQW electric dipole momentum eD , where D is interwell distance (signs correspond to two possible locations of e and h in two wells). In the case of identical quantum wells SDE and SIE have two-fold degeneracy. We suppose also that the uncertainty of exciton wave vector due to CQW roughness etc. is much smaller than all momenta involved in the problem. In the absence of external fields SDE is the lowest excitonic state.

Electric and magnetic fields change the dispersion of SIE [2,8,9] (Fig.1 b). Normal electric field splits SIE sublevels as $\Delta E = eD E = \hbar$ due to electric dipole - electric field interaction. It can be shown that moving SIE has in-plane magnetic dipole momentum $\frac{eD p}{cM}$ normal to its velocity, where p is in-plane momentum and M is a mass of the SIE. Thus in parallel magnetic field SIE sublevel dispersion curves move oppositely apart from the center of Brillouin zone by the quantity of $K_m = \frac{eD \hbar}{c\hbar}$ due to velocity-selective magnetic dipole - magnetic field interaction [10]. This was experimentally observed in the work [9]. SDE level, as in electric field, remains unchanged and degenerated.

Thus, by in-plane magnetic and normal electric fields one can change SIE sublevel position in dispersion space. In particular, applying normal electric field makes it possible for one of the SIE sublevels to become the ground state of the excitonic system (instead of SDE at $E=0$).

The process of recombination of excitons with emitting a photon is possible only inside the radiative zone - a small area in the center of Brillouin zone with $k < k_r = E_g/(c\hbar)$, where E_g is the energy gap in semiconductor, c is the speed of light in the media and k_r is the boundary wave vector of the radiative zone (in GaAs $k_r = 3 \text{ } \mu\text{m}^{-1}$). This is due to photon inability to carry away an in-plane momentum greater than k_r . Out of the radiative zone the process of photon recombination of the exciton is forbidden, and the process of exciton recombination with production

of an acoustic phonon and a photon becomes the most probable exciton recombination process [11]. This process is of the second order of magnitude of the exciton interaction with photon and acoustic phonon fields. Greatest parts of energy and 2D momentum of exciton are carried away by photon and phonon, correspondingly.

From preceding discussion, the following scheme of the observation of BEC of SIE can be developed. In the presence of such normal electric and in-plane magnetic fields that SIE is the ground excitonic state with minimum of its dispersion curve situated out of the radiative zone, SIE ground level is being pumped by laser radiation into the radiative zone (Fig. 2a). After laser switch off the system is evolving using two channels – one part of pumped excitons in radiative zone recombines with production of photons, and the other part of excitons relaxate into the minimum of dispersion of SIE level out of the radiative zone, transferring their extra energy and momentum to acoustic phonons (Fig. 2b). Thereafter, the system of SIE reaches a quasi-equilibrium state with the temperature of reservoir (lattice), and in case of sufficiently low temperature of lattice the system of SIE forms BEC. We will consider $T = 0$ for simplicity; at temperatures much less than Kosterlitz-Thouless temperature optical properties are changed only slightly with respect to those at $T = 0$. The state of the system at this moment of evolution is the state where almost all excitons are at SIE level in its dispersion minimum with wave vector K_m (for low density of excitons) and all the other levels are not populated. In high magnetic field we have $K_m = k_r$ (e.g. $H = 10T$ and $D = 10nm$ corresponds to $K_m = 2 \cdot 10^8 m^{-1}$).

Bose-condensed SIE situated in momentum space at $K = K_m$ position are "dark", that is the process of emitting of photons is weak. The rate of recombination SIE in BEC through intermediate production of virtual exciton in radiative zone (with production of photon and phonon with wave vectors in the region of momentum space $d^3q; d^3k$) is

$$dW_{phn;pht} = \frac{P}{s} \frac{(M_{s;pht} M_{s;phn})^2}{(|\psi_{pht}(k) - \psi_s(k)|)^2 + \frac{2}{s}} + \frac{P}{2(|\psi_{pht}(k) - \psi_{s_1}(k) + i s_1}(|\psi_{pht}(k) - \psi_{s_2}(k) + i s_2})} + c.c. : \frac{M_{s_1;pht} M_{s_1;phn} M_{s_2;pht} M_{s_2;phn}}{2(|\psi_{pht}(k) - \psi_{s_1}(k) + i s_1}(|\psi_{pht}(k) - \psi_{s_2}(k) + i s_2})} + c.c. : \frac{N_k! N_q!}{(k + q - K_m)! (pht(k) + phn(q) - SIE(K_m))!} d^3q d^3k \quad (1)$$

In Eq.(1) is 2D density of SIE in CQW; $N_k!; N_q!$ are numbers of photons and phonons in the states with wave vectors k and q , correspondingly; notation x implies 2D in-plane vector x or in-plane component of 3D vector x ; $M_{s;phn}$ is the matrix element of transformation of SIE into s -state exciton in radiative zone with acoustic phonon creation, and $M_{s;pht}$ is the matrix element of photon recombination of s -exciton in radiative zone; s is the width of s th exciton level. Using GAA parameters, we estimate for SDE $SDE = 10^{10} sec^{-1}$. Recombination rate consists of resonant terms, corresponding to the processes with intermediate creation of virtual s -exciton in radiative zone, and nonresonant terms.

Main contribution to the rate of SIE recombination process is originated from recombination transitions, in which virtual s -excitons are mostly close to their mass shell. SIE and SDE are such s -excitonic states in our case. At this moment of evolution (Fig.2b) the process goes mainly through virtual SIE in radiative zone. For the estimation we take phonon energy to be equal to $\psi_{phn}(q) = c_s K_m$, where c_s is a speed of sound. In this case $\psi_{pht}(k) = \psi_{SIE}(K_m) - c_s K_m$ and we get:

$$W_{phn;pht} = \frac{(M_{SDE;pht} M_{SDE;phn})^2}{(c_s K_m - (\psi_{SIE}(K_m) - \psi_{SDE}(0)))^2 + \frac{2}{SDE}} + \frac{(M_{SIE;pht} M_{SIE;phn})^2}{(c_s K_m - (\psi_{SIE}(K_m) - \psi_{SIE}(0)))^2 + \frac{2}{SIE}} \quad (2)$$

In this formula we also neglected non-resonant terms. Parameter $(\psi_{SIE}(K_m) - \psi_{SIE}(0))$ is not dependent on electric field magnitude, while $(\psi_{SIE}(K_m) - \psi_{SDE}(0))$ is a linear function of electric field magnitude, and equals zero when the electric field has a particular (resonant) value. For CQW system used in Ref. [9] at magnetic field 10T these parameters are correspondingly equal to $0.8 \cdot 10^8 sec^{-1}$ and $3.5 \cdot 10^8 sec^{-1}$.

At this stage of the system evolution one can reduce the magnitude of electric field down to the moment, when the conservation laws for energy and 2D momentum are satisfied in the processes of SIE in BEC transformation into real SDE in radiative zone with production of acoustic phonon and SDE in radiative zone photon recombination (Fig.2c) (in other words, when resonance condition is satisfied). Using Eq.(2), one can get the estimation for the ratio of PL rates at initial condition and after tuning to the resonance in the system used in Ref. [9]:

$$\frac{W_{resonance}}{W_{initial}} = \frac{2(\psi_{SIE}(K_m) - \psi_{SIE}(0))^2}{\frac{2}{SDE}} \cdot 10^5 \cdot 6 \cdot 2; = \frac{M_{SDE;pht} M_{SDE;phn}}{M_{SIE;pht} M_{SIE;phn}} \quad (3)$$

Matrix elements of phonon-exciton interaction vertex are determined by Bardeen-Shockley deformational potential Ref. [12]. Matrix element of photon recombination of an exciton in radiative zone is proportional to the overlapping integral of e and h in the exciton [11]. Using Eq.(3) one can show that PL intensity can be increased, by changing the electric field, at least by two orders. Therefore, after tuning the system to the resonance the recombination rate will be greatly increased, and this will result in sharp PL intensity growth.

Now we will analyze angular dependence of resonant PL. Let magnetic field be directed along x-axis. In this case \mathbf{K}_m vector is parallel to y-axis. Studying resonant radiation, in Eq.(1) we take only resonant term responsible for SIE recombination by intermediate SDE creation. Integrating (1) over d^3q , we obtain the rate of photon emission in k-space area d^3k :

$$dW_{\text{ph}}^{\text{res}} = \frac{h}{(k_{\text{ph}}(k) + k_{\text{SDE}}(k))^2 + \frac{2}{\text{SDE}}} \frac{(\epsilon_{\text{SIE}}(\mathbf{K}_m) + \epsilon_{\text{ph}}(k)) d^3k}{(\epsilon_{\text{SIE}}(\mathbf{K}_m) + \epsilon_{\text{ph}}(k))^2 - c_v^2(\mathbf{K}_m + \mathbf{k})^2} \quad (4)$$

The maximum energy of the photon is $hc \frac{\epsilon_{\text{SIE}}(\mathbf{K}_m) + c_v K_m}{c + c_v}$. Photons with any energy less than its maximum value can be created in the process, but the rate of production of photons with small energy is suppressed by Lorentz factor.

The process becomes resonant in the case when the maximum of the Lorentz factor and the singularity of the second factor coincide for at least some values of \mathbf{k} . This condition can be made clear graphically (Fig.3a). Resonant condition is satisfied if in the space $(\mathbf{P}; \mathbf{k})$ a dispersion cone of 2D phonon, drawn down from BEC position, intersects SDE dispersion surface in the radiative zone. We stress, that 2D dispersion of 3D phonons gives only the minimum energy of a phonon with a given component of 3D wave vector on CQW plane (the same is true for photons). The minimum energy corresponds to zero normal to CQW component of phonon wave vector. For this reason, resonant process with SIE recombination with intermediate creation of real SDE takes place even in case of greater energy of exciton in BEC than resonance one (i.e. in smaller electric fields), but with less intensity.

The resonance condition corresponds to a distinct range of electric field magnitude. We represent exciton in BEC energy dependence on electric field magnitude as $\epsilon_{\text{SIE}}(\mathbf{K}_m) = c_v(K_m + 1) = 2k_r T(E)$, where $T(E)$ is a linear function of electric field. Since $K_m = k_r$, we can admit that in the case of resonance, 2D phonon dispersion (cone) intersects the SDE dispersion surface in a circle (Fig.2 b):

$$(k_x - k_0)^2 + k_y^2 = k_r k_0 T(E) + k_0^2; \quad k_0 = \frac{M c_v}{h} \quad (5)$$

For GaAs we have $k_0 = 10^5 \text{ cm}^{-1}$. The condition of the resonance can be represented as $2 + \frac{k_r}{k_0} T(E) = \frac{k_0}{k_r}$.

We will below admit resonance approximation, i.e. substitution for the Lorentz factor by delta-function $\delta(\epsilon_{\text{ph}}(k) - \epsilon_{\text{SDE}}(k))$. This approximation is valid when $\text{SDE} \ll c_v k_r$, so that it is applicable in our case since $c_v k_r = 1.5 \cdot 10^4 \text{ sec}^{-1}$. In result one can get:

$$dW_{\text{ph}}^{\text{res}}(\mathbf{k}; \mathbf{k}) = \frac{d}{T(E) \sin^2(\theta) \sin^2(\phi) \cos(\phi)}; \quad \theta = k_r = k_0 = 3 \quad (6)$$

Here d is the spatial angle, θ and ϕ are azimuth and polar angles of spherical coordinates in photon wave vector \mathbf{k} space. Azimuth axis ($\phi = 0$) is directed parallel to \mathbf{K}_m . Eq. (6) gives a resonant radiation angular dependence. Resonant PL is absent when $T(E) < k_0/k_r$. At resonance ($2 + k_r/k_0 T(E) = k_0/k_r$) resonant photons are emitted into spatial angle, which is formed by intersection of sphere with radius k_r and a cylinder with base (5) and generatrix parallel to z-axis (Fig.3 c). In the resonant approximation on boundary of this spatial angle the rate of resonant PL has an integrating singularity. It can be shown that real rate of PL right on this boundary is approximately as much as $\frac{c_v k_r}{\text{SDE}} \approx 15$ times greater than in the other area of spatial angle of the resonant radiation. If $T(E) > 2 + k_r/k_0$ resonant PL intensity has no singularity on the boundary of spatial angle of resonant PL, and with increasing $T(E)$ (reducing electric field) tends to become more and more isotropic.

When resonance condition is satisfied, energy level scheme of our system is similar to that of three-level in pulse one-pass laser with inverse population of upper level and with rapid lower transition (Fig.4 a). Rapidity of the lower transition with respect to the rate of upper transition is supplied by tunneling character of transformation of SIE into SDE with creation of acoustic phonon. The difference is that in our case phonons are emitted instead of photons. Wave vectors of resonant phonons form a prolate ellipsoid of revolution with base (5) and the ratio of radii $K_m = k_0$ (Fig.4 b). The best quality of unidirectivity and monochromatism of the resonant phonons is evidently achieved in electric field that corresponds to the relation $T(E) = k_0/k_r$, when the ellipsoid reduces to a point, so that for discussion of phonon "laser" radiation we will consider this case.

At this resonance condition the coherence of resonant phonons at early stages of the process of phonon emission is determined by total (in a sense "homogeneous" and "inhomogeneous") width of phonons. Width of wave vector distribution of phonons can be represented as $q = k_0 (q_{\text{hom}} + q_{\text{inh}})$, where q_{hom} is due to widths of SDE level and phonon state, and q_{inh} is connected with SIE momenta spread that corresponds to depleting of BEC due

to interactions of excitons; $q_{inh} = \frac{P}{U(0)M} = h$, where $U(0)$ is zero Fourier component of interaction between SIE; $q_{hom} = (s_{DE} + \gamma_{phn})C_v^{-1}$, where γ_{phn} is the phonon attenuation rate.

There are two sufficient conditions for phonon radiation to be the "laser" one: generation condition and condition of macroscopic population of each phonon state. In our case the first condition is the prevailing rate γ_{spont} of spontaneous phonon emission in the process over the rate of phonon attenuation in the sample γ_{phn} . Attenuation of the phonon is determined by the media properties, temperature, the size of the sample and scattering of phonon on the planes of CQW. Using data from Ref. [9] and Eq.(3) one can get, that γ_{spont} can be not simply greater than the phonon attenuation rate, but even can reach the phonon energy $K_m C_v = 10^{12} \text{sec}^{-1}$.

The second condition is macroscopic population of each phonon quantum state (when all SIE in BEC are recombined and thus have contributed to phonon radiation). Phonon radiation occupies $V(q)^3 = (2\pi)^3$ quantum states, where V is a volume of the sample, while the number of SIE is S , S is the area of CQW. The condition is $L_z (2\pi)^3 = (k_0 (U(0)M = h + q_{hom}))^{3=2}$, where L_z is the width of the sample in z -direction. The quantity L_z appeared due to that phonons and SIE differ in their dimensions (3D phonons vs. 2D excitons).

In conclusion we emphasize that discussions above point out possible existence of interesting effect - "phonon laser" (details will be published elsewhere). Using all advantages of the analogy with photon laser, one can propose to adjust a phonon resonator for the purpose of increasing phonon coherence. The resonator can experimentally be realized as phonon mirrors (the media with greater speed of sound) on (y -direction) edges of the sample. In this case one-pass phonon "laser" becomes multipass one. The restriction for the width of the sample (second condition) can be made weaker by considering heterostructure consisting of many CQW (the distance between CQW must satisfy the above condition for L_z).

Note that, coherent phonons modulate the dielectric function of the media. This gives an opportunity of detection of the effect of coherent phonon generation by study the modulation of optical properties of the media, which can be observed by time-resolved femtosecond spectroscopy (e.g. by pump-probe method). Another possibility to observe coherent properties of phonon radiation is analysis of its statistics, e.g. by Hurlbut-Brown and Twiss method.

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Captures to Figures.

Fig.1 Dispersion laws of direct and indirect excitons in coupled quantum wells a) Without external electromagnetic fields SDE level is lower than SIE level by the difference of Coulomb interactions in SDE and SIE b) In parallel magnetic field SIE sublevel dispersions move oppositely apart by wave vector $K_m = \frac{eH D}{ch}$; in normal electric field one of SIE sublevels lowers as $\Delta = eED = \hbar$ and the other rises as Δ

Fig.2 a) Laser pumping of SIE level in the presence of parallel magnetic and normal electric fields. $K_m = \frac{eH D}{ch}$ is the displacement of dispersion minimum in parallel magnetic field, k_r is boundary wave vector of radiative zone. b) Relaxation of indirect excitons. One part of excitons recombines with production of photons, and the other part relaxates to the minimum of SIE dispersion K_m . c) Changing of BEC position when electric field magnitude is being reduced.

Fig.3 a) Position of direct and indirect exciton dispersions when condition of the resonance is satisfied. b) intersection of dispersion surface of indirect excitons with 2D phonon dispersion. c) segments of spatial angle correspond to the boundary of resonant photoluminescence angular dependence.

Fig.4 a) Three-level laser analog of phonon laser. b) Phonon wave vector distribution. Wave vectors of phonons form prolate ellipsoid of revolution with ratio of its radii $\frac{K_m}{k_0}$.

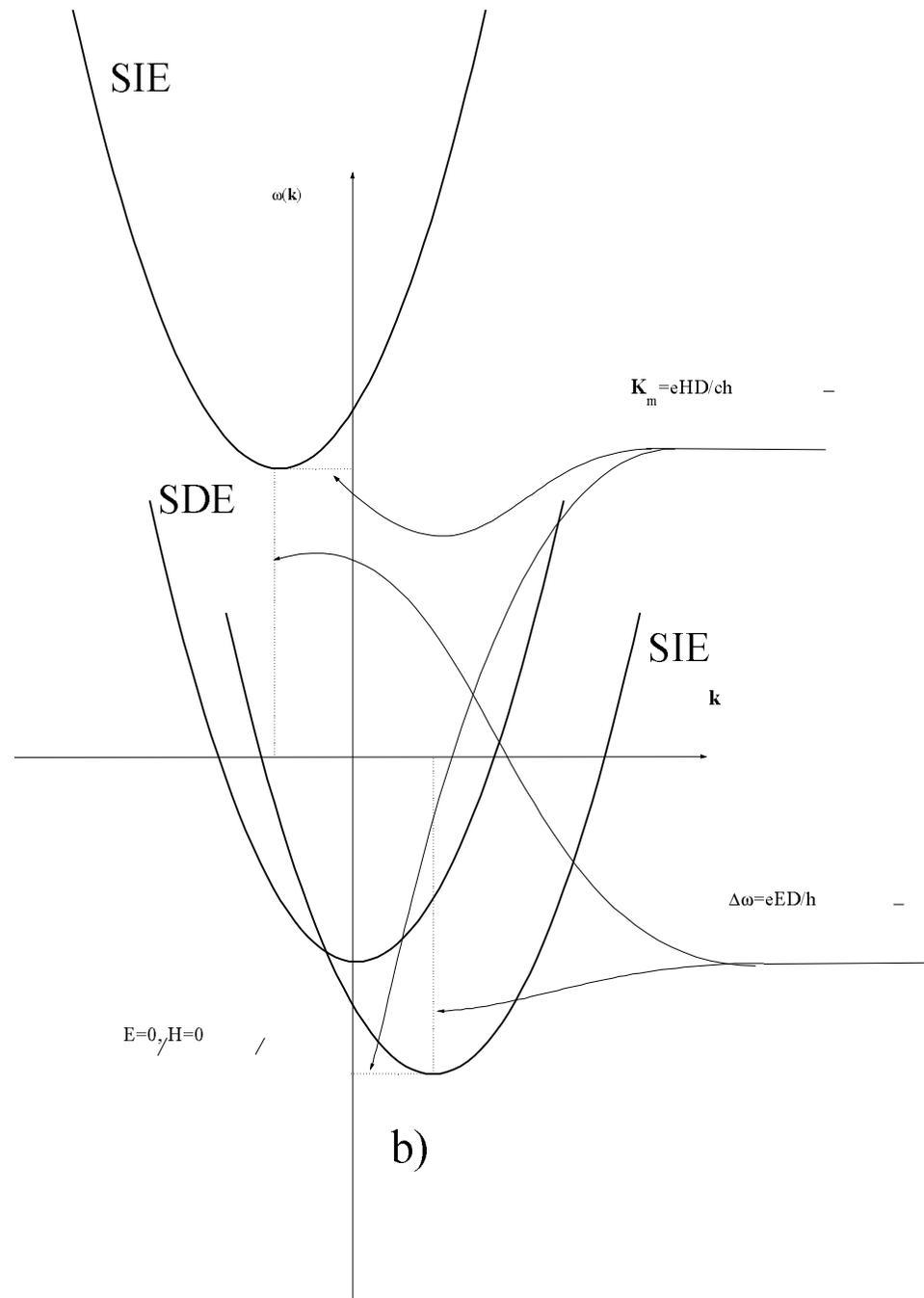
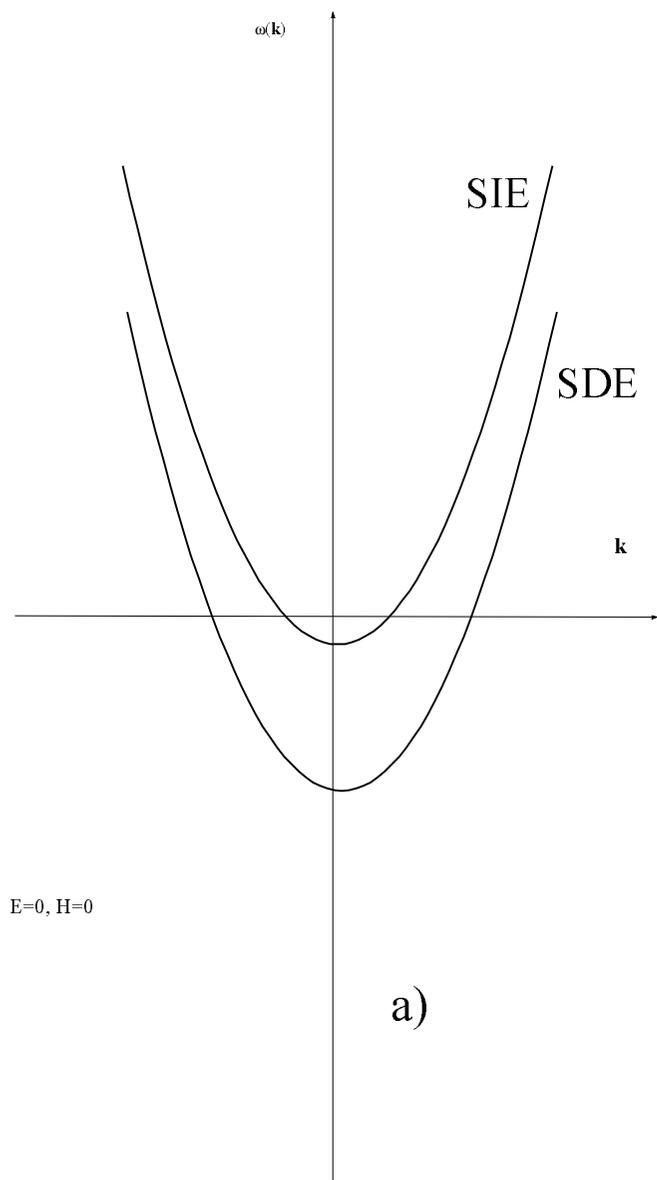


Fig.1

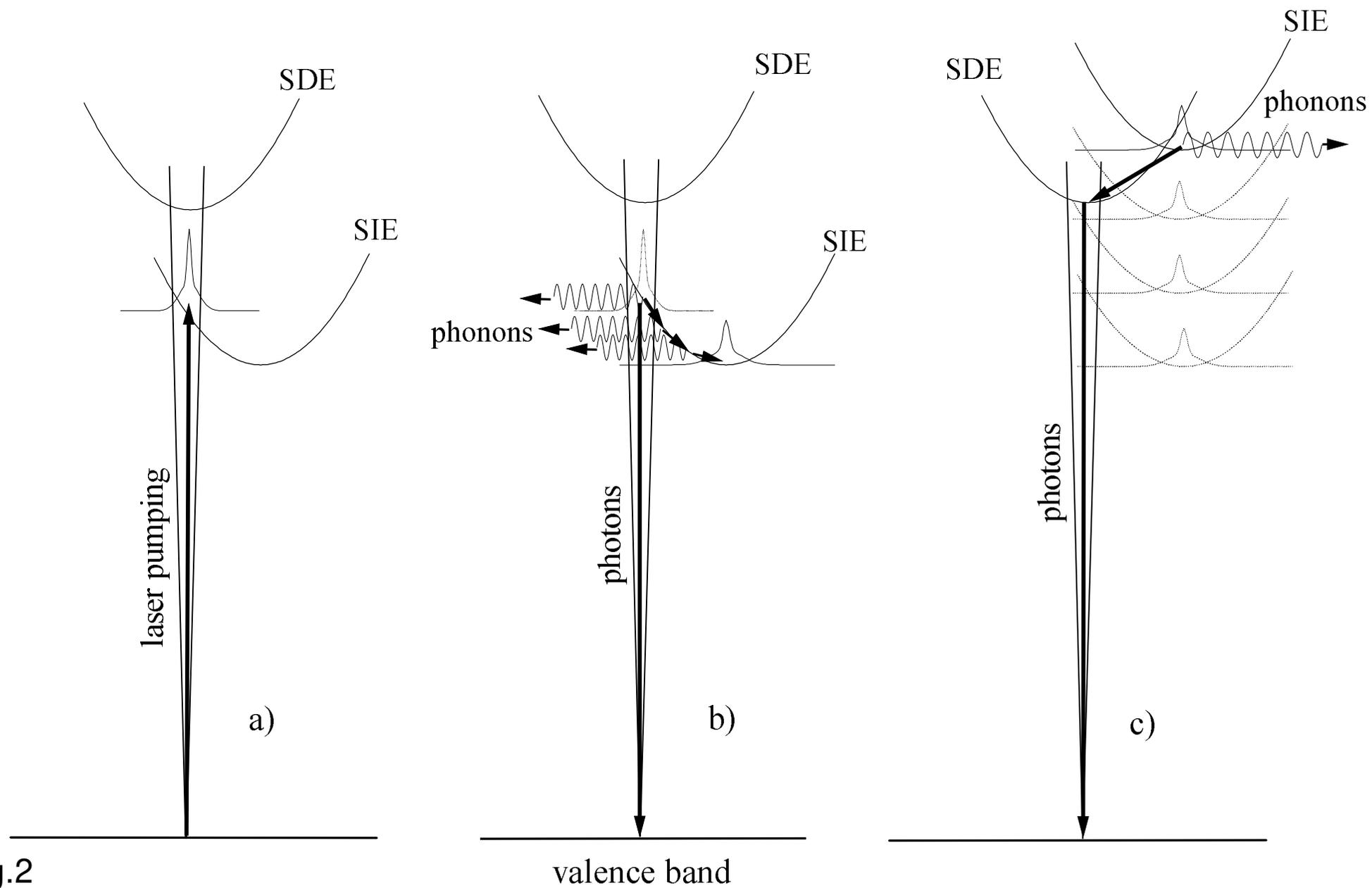


Fig.2

valence band

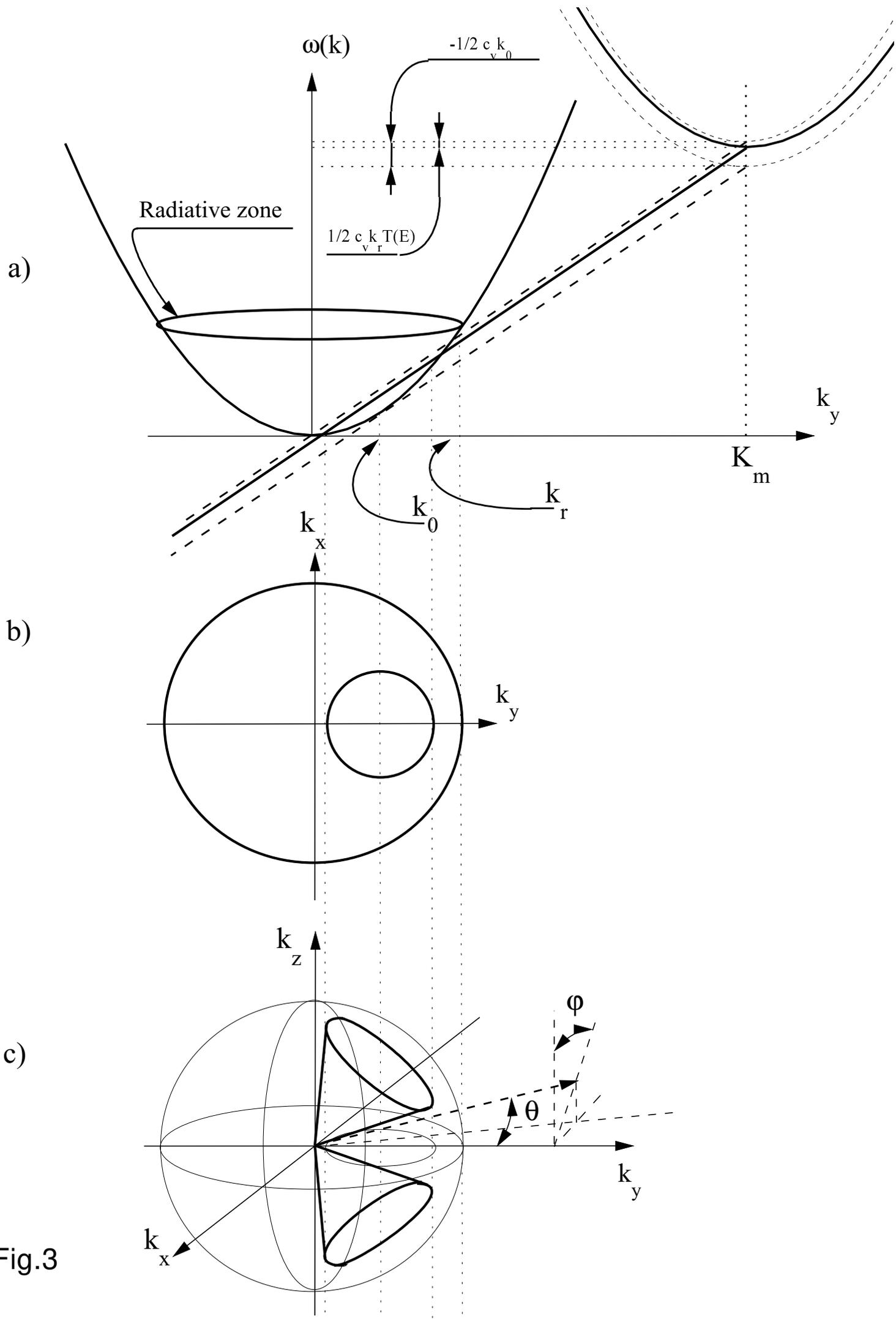
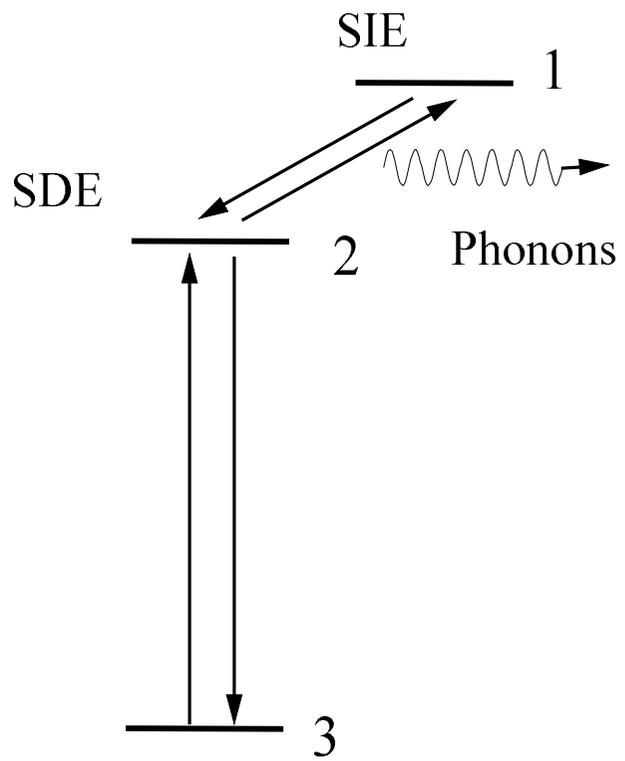
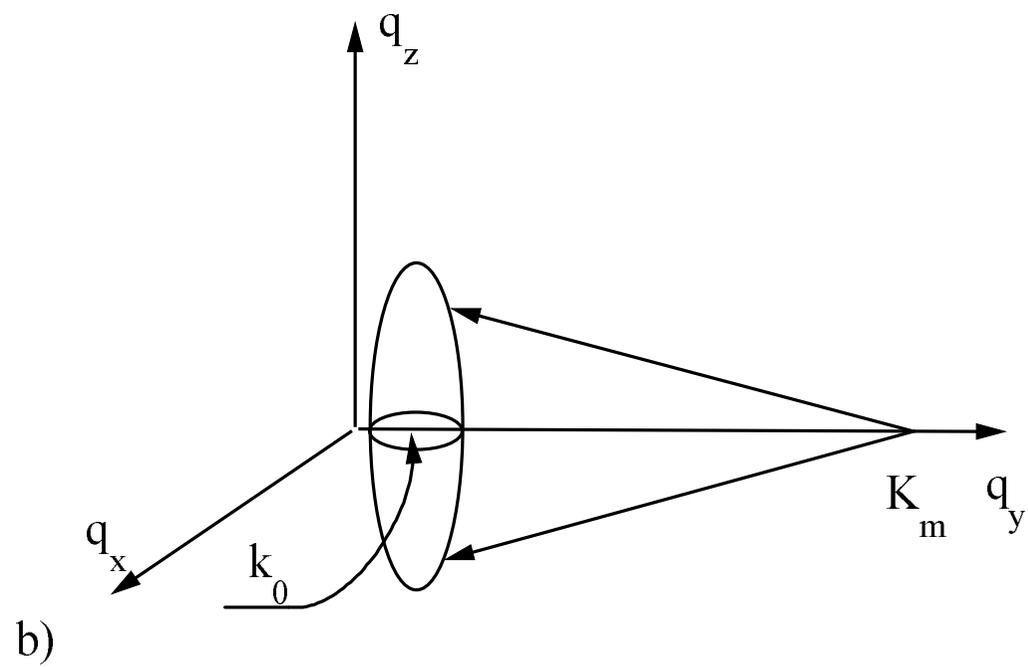


Fig.3



a)



b)

Fig.4

